Amendments to the Claims

1. (*Currently Amended*) An electric device ~~(1, 100)~~ with a body ~~(2, 101)~~ having:

[[-]] a resistor ~~(36, 250)~~ comprising a phase change material which is able to be in a first phase and in a second phase, the resistor ~~(36, 250)~~ having a surface with a first contact area ~~(5, 132)~~ and a second contact area ~~(6, 272)~~, the resistor ~~(36, 250)~~ having an electrical resistance between the first contact area ~~(5, 132)~~ and the second contact area ~~(6, 272)~~, the electrical resistance having a first value when the phase change material is in the first phase and a second value when the phase change material is in the second phase,

[[-]] a first conductor ~~(3, 130)~~ electrically connected to the first contact area ~~(5, 132)~~,

[[-]] a second conductor ~~(4, 270)~~ electrically connected to the second contact area ~~(6, 272)~~,

[[-]] the first conductor ~~(3, 130)~~, the second conductor ~~(4, 270)~~ and the resistor ~~(36, 250)~~ being able to conduct a current for heating of the phase change material to enable a transition from the first phase to the second phase, and

[[-]] a layer ~~(20, 39, 126, 140, 260)~~ of a dielectric material for reducing a heat flow to parts of the body ~~(2, 101)~~ free of the resistor ~~(36, 250)~~ during the heating, the dielectric material comprising a porous material with pores having a size between 0.5 and 50 nm.

2. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in claim 1, wherein the pores have a size between 1 and 10 nm.

3. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in claim 1, wherein the pores are substantially free of water.

4. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in claim 1, wherein the pores have hydrophobic surfaces.

5. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in claim 4, wherein the porous material comprises an organosilicate and the hydrophobic surfaces have hydrocarbyl groups.

6. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in claim 5, wherein the porous material is obtainable by

~~[[-]]~~ applying a liquid layer of a composition comprising tetra-alkoxysilane, hydrocarbylalkoxysilane, a surfactant and a solvent onto a substrate, wherein the molar ratio between tetra-alkoxysilane and hydrocarbylalkoxysilane is 3:1 at the most, and

~~[[-]]~~ heating the liquid layer to remove the surfactant and the solvent and to form the hydrophobic porous layer.

7. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in claim 6, characterized in that the surfactant is a cationic surfactant, and the surfactant and the totality of alkoxysilanes are present in a molar ratio greater than 0.1:1.

8. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in claim 1, characterized in that the porous material has a porosity above 20 percent.

9. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in claim 1, characterized in that the resistor ~~(36, 250)~~ is embedded in the body ~~(2, 101)~~, the layer ~~(39, 126, 140, 260)~~ being in direct contact with the resistor ~~(36, 250)~~.

10. (*Currently Amended*) An electric device ~~(100)~~ as claimed in claim 9, characterized in that the first contact area ~~(132)~~ is smaller than the second contact area ~~(272)~~, and the first conductor ~~(130)~~ comprises a part in direct contact with the first contact area ~~(132)~~, the part being embedded in the layer ~~(126, 140)~~.

11. (*Currently Amended*) An electric device ~~(1, 100)~~ as claimed in claim 1, characterized in that the first conductor ~~(3, 130)~~, the second conductor ~~(4, 270)~~, the resistor ~~(36, 250)~~ and the layer ~~(20, 39, 126, 140, 260)~~ constitute a memory element ~~(30, 103)~~, and the body ~~(2, 101)~~ comprises:

~~[[-]]~~ an array of memory cells, each memory cell comprising a respective memory element (30, 103) and a respective selection device (26, 104), and

[[-]] a grid of select lines ~~(12, 42, 120, 190)~~, each memory cell being individually accessible via the respective select lines ~~(12, 42, 120, 190)~~ connected to the respective selection device ~~(26, 104)~~.

12. (*Currently Amended*) An electric device ~~(100)~~ as claimed in claim 11, characterized in that:

[[-]] the selection device ~~(104)~~ comprises a metal oxide semiconductor field effect transistor having a source region ~~(110)~~, a drain region ~~(112)~~ and a gate region ~~(116)~~, and

[[-]] the grid of select lines comprises N first select lines ~~(190)~~,

M second select lines ~~(120)~~, N and M being integers, and

an output line ~~(271)~~, the first conductor ~~(130)~~ of each memory element ~~(103)~~ being electrically connected to a first region selected from the source region ~~(110)~~ and the drain region ~~(112)~~ of the corresponding metal oxide semiconductor field effect transistor, the second conductor ~~(270)~~ of each memory element ~~(103)~~ being electrically connected to the output line ~~(271)~~, a second region of the corresponding metal oxide semiconductor field effect transistor which is selected from the source region ~~(110)~~ and the drain region ~~(112)~~ and which is free from the first region, being electrically connected to one of the N first select lines ~~(190)~~, the gate region ~~(116)~~ being electrically connected to one of the M second select lines ~~(120)~~.